



Appendix to Amendment of March 18, 2003

IN THE SPECIFICATION:

Please replace the paragraph beginning at page 12, line 6, with the following paragraph:

Fig. 8 illustrates an ESD device 600 constructed according to a fourth embodiment of the present invention. With reference to Fig. 8, device 600 includes a single island 602 in and along drain region 412 and adjacent gate 414, and a single island 602 in and along drain region 412 and adjacent gate 416. The left end of island 602 extends beyond the left edge of region 406 while the right end of island 602 is proximate the right edge of region 406 but within region 406. Island 604 is non-symmetrically disposed relative to island 602 in that the right end of island 604 extends beyond the right edge of region 406 while the left end of island 604 is within region 406. Thus, islands 602 and 604 are non-symmetric about axis A-A' and axis B-B'.

IN THE CLAIMS:

Please amend claim 1 as follows:

1. (Amended) An electrostatic discharge (EDS) protection device, comprising:
a semiconductor layer;
a first diffusion region formed in the layer;
a second diffusion region formed in the layer adjacent to and spaced apart from the first diffusion region; [and]
a channel region formed between the first and second diffusion regions; and

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at least one island formed in [along a length direction of] the first diffusion region,
the at least one island being positioned non-symmetrically [along the length direction]
with respect to a symmetry axis, wherein
said symmetry axis extending from a midpoint of the channel region
perpendicular to the channel region) and in parallel to a surface of the semiconductor
layer.

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